



30V 4 IN 1 N-Channel MOSFETs

General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BV_{DSS}	$R_{DS(ON)}$	I_D
30 V	10.2 mΩ	35 A

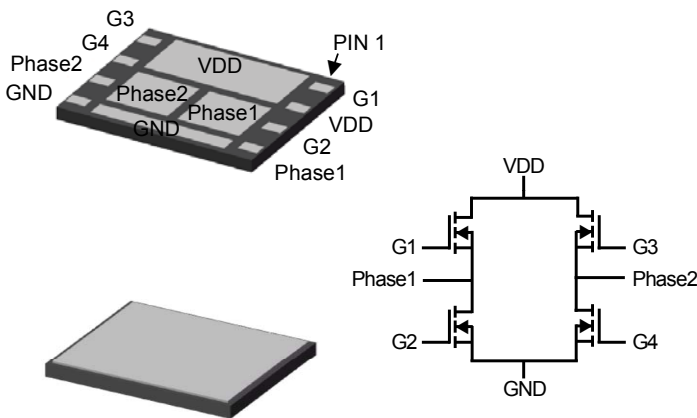
Features

- $R_{DS(ON)} \leq 10.2m\Omega @ V_{GS}=10V$
- Fast switching
- Improved dv/dt capability
- Green Device Available

Applications

- Full Bridge Applications

DFN5X6 Pin Configuration



Absolute Maximum Ratings $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current - Continuous ($T_C=25^\circ C$)	35	A
	Drain Current - Continuous ($T_C=100^\circ C$)	22	A
I_{DM}	Drain Current - Pulsed (NOTE 1)	140	A
EAS	Single Pulse Avalanche Energy (NOTE 2)	13	mJ
IAS	Single Pulse Avalanche Current (NOTE 2)	16	A
P_D	Power Dissipation ($T_C=25^\circ C$)	21.5	W
	Power Dissipation - Derate above $25^\circ C$	0.17	W/ $^\circ C$
T_J	Operating Junction Temperature Range	-50 to 150	$^\circ C$
T_{STG}	Storage Temperature Range	-50 to 150	$^\circ C$
Marking Code		NC010	

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	5.8	$^\circ C/W$



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Electrical Characteristics (T_J=25°C, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =30V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =30V, V _{GS} =0V, T _J =125°C	---	---	10	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA

On Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
R _{DS(ON)}	Static Drain-Source On-Resistance (NOTE 3)	V _{GS} =10V, I _D =10A	---	8.4	10.2	mΩ
		V _{GS} =4.5V, I _D =5A	---	11.6	15	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	1.8	2.5	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =3A	---	6.4	---	S

Dynamic and switching Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =10V, I _D =5A (NOTE 3、4)	---	16.5	33	nC
Q _{gs}	Gate-Source Charge		---	2.3	5	
Q _{gd}	Gate-Drain Charge		---	3	6	
T _{d(on)}	Turn-On Delay Time	V _{DD} =15V, V _{GS} =10V, R _G =6Ω, I _D =1A (NOTE 3、4)	---	3.8	7	nS
T _r	Rise Time		---	10	19	
T _{d(off)}	Turn-Off Delay Time		---	22	42	
T _f	Fall Time		---	6.6	13	
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, F=1MHz	---	620	900	pF
C _{OSS}	Output Capacitance		---	85	125	
C _{rss}	Reverse Transfer Capacitance		---	60	90	
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	---	2.8	5.6	Ω

Drain-Source Diode Characteristics and Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	35	A
I _{SM}	Pulsed Source Current (NOTE 3)		---	---	70	A
V _{SD}	Diode Forward Voltage (NOTE 3)	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1	V

NOTES :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=16A, R_G=25Ω, Starting T_J=25°C.
3. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.



Characteristics Curves

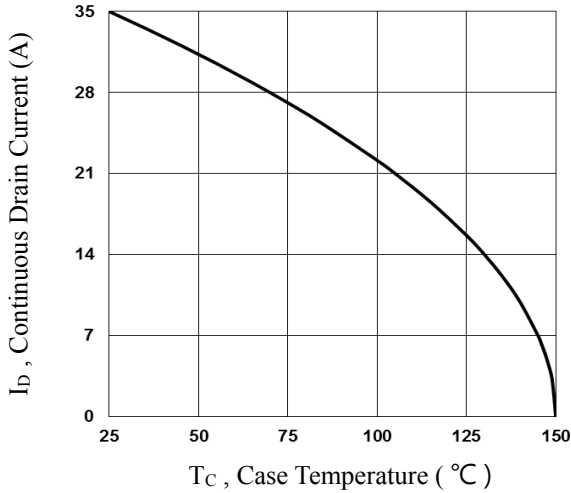


Fig.1 Continuous Drain Current vs. T_C

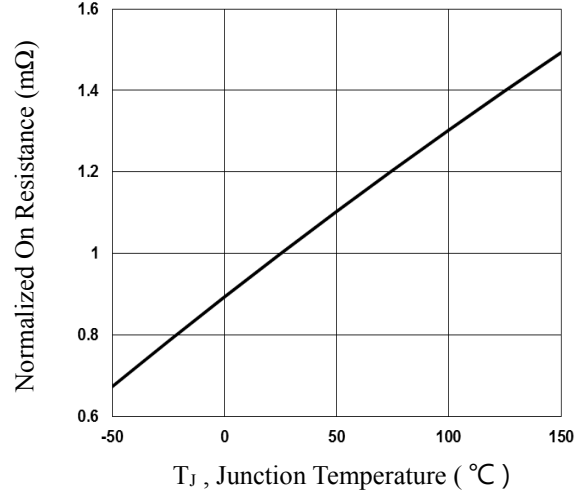


Fig.2 Normalized RDSON vs. T_J

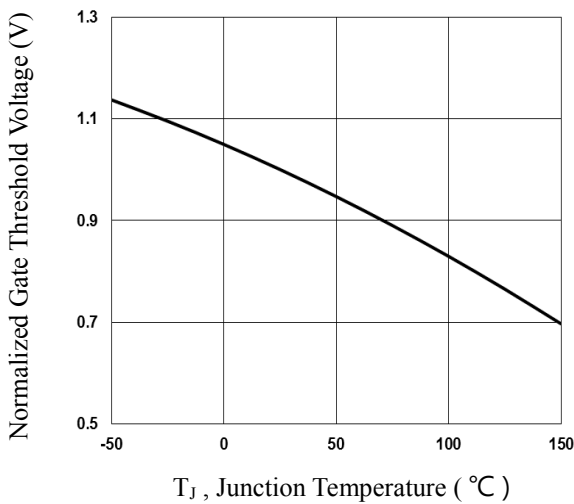


Fig.3 Normalized V_{th} vs. T_J

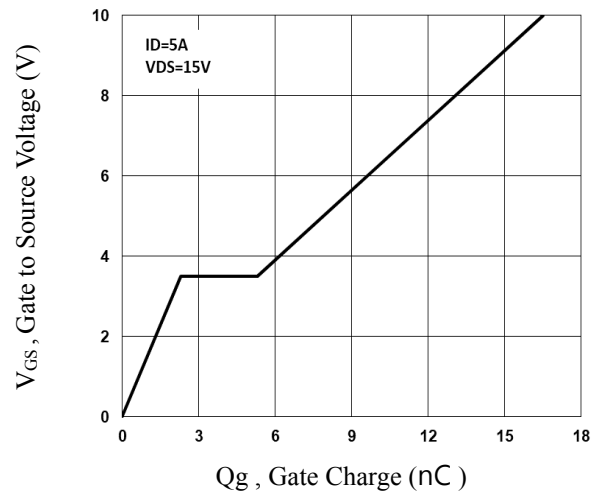


Fig.4 Gate Charge Waveform

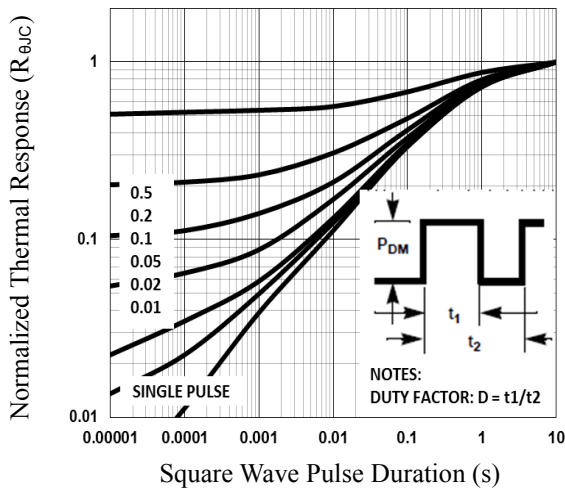


Fig.5 Normalized Transient Response

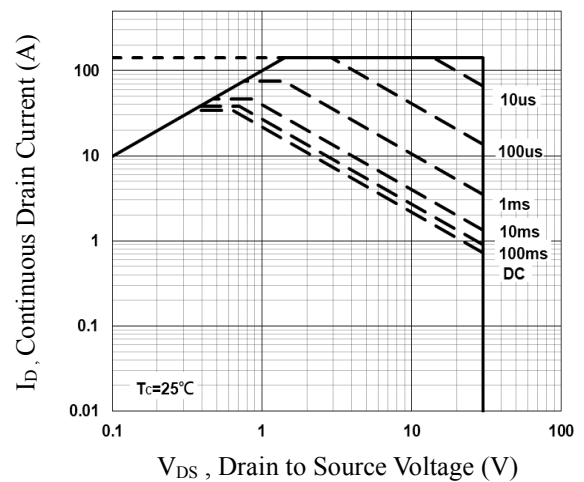


Fig.6 Maximum Safe Operation Area



Characteristics Curves

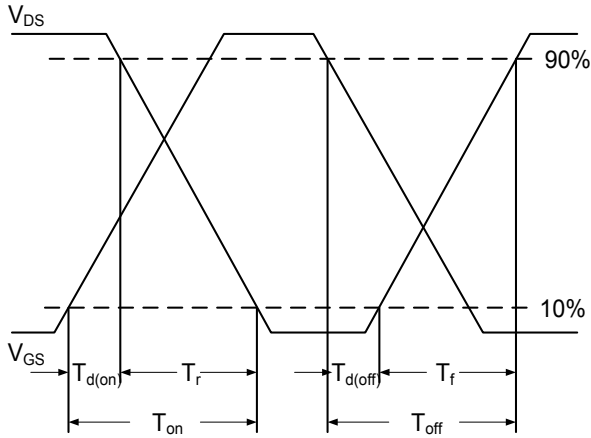


Fig.7 Switching Time Waveform

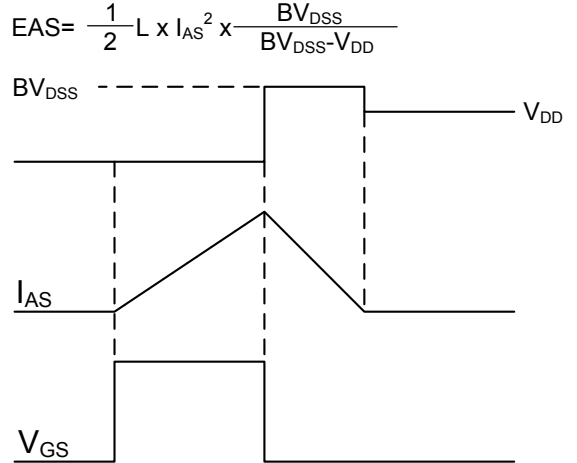
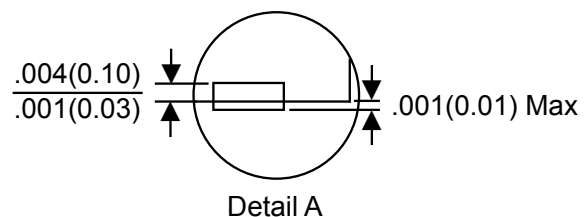
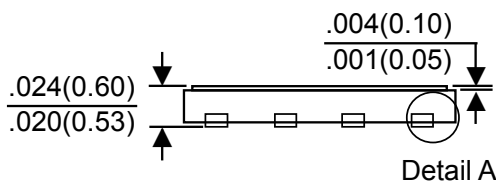
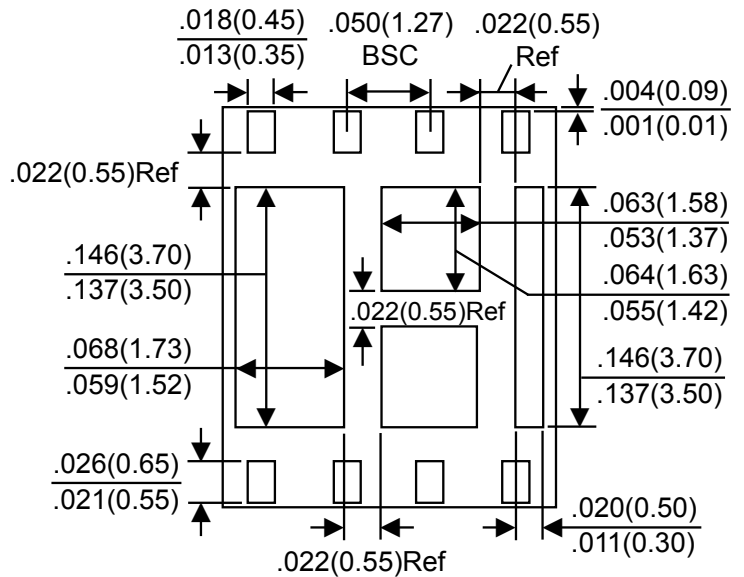
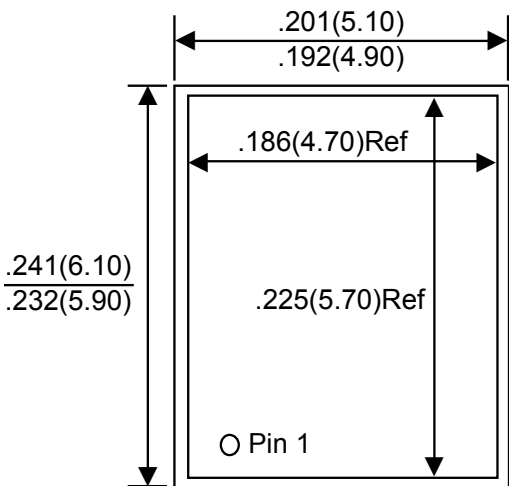


Fig.8 EAS Waveform

Package Outline Dimensions



DFN5X6

Dimensions in inches and (millimeters)



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